CLAIMS

1. A film-like article comprising:

a thin film integrated circuit which can store information described on the film-like article; and

an antenna connected to the thin film integrated circuit,

wherein the thin film integrated circuit and the antenna are mounted inside the film-like article.

2. A film-like article comprising:

a thin film integrated circuit which can store information described on the film-like article; and

an antenna connected to the thin film integrated circuit,

wherein the thin film integrated circuit is mounted inside the film-like article, and the antenna is mounted on a surface of the film-like article.

3. A film-like article according to Claim 1,

wherein when the thickness of the film-like article is D, the position to dispose the thin film integrated circuit X may be set so as to satisfy $(1/2)\cdot D - 30\ \mu m < X < (1/2)\cdot D + 30\ \mu m$.

4. A film-like article according to Claim 2,

wherein when the thickness of the film-like article is D, the position to dispose the thin film integrated circuit X may be set so as to satisfy $(1/2)\cdot D - 30\ \mu m < X < (1/2)\cdot D + 30\ \mu m$.

5. A film-like article comprising:

a thin film integrated circuit which can store information described on the film-like article; and

an antenna connected to the thin film integrated circuit,

wherein the thin film integrated circuit and the antenna are mounted on a surface of the film-like article.

6. A film-like article comprising:

a thin film integrated circuit which can store information described on the film-like article; and

an antenna connected to the thin film integrated circuit,

wherein the thin film integrated circuit is mounted on a surface of the film-like article, and

the antenna is mounted inside the film-like article.

7. A film-like article comprising a thin film integrated circuit which can store information described on the film-like article,

wherein the film-like article is provided with a depression, and

the thin film integrated circuit includes an antenna.

8. A film-like article according to Claim 1,

wherein an opening with slits is provided in a connection area between the thin film integrated circuit and the antenna.

9. A film-like article according to Claim 2,

wherein an opening with slits is provided in a connection area between the thin film integrated circuit and the antenna.

10. A film-like article according to Claim 5,

wherein an opening with slits is provided in a connection area between the thin film integrated circuit and the antenna.

11. A film-like article according to Claim 6,

wherein an opening with slits is provided in a connection area between the thin film integrated circuit and the antenna.

12. A film-like article according to Claim 7,

wherein an opening with slits is provided in a connection area between the thin film integrated circuit and the antenna.

13. A film-like article according Claim 1,

wherein the thin film integrated circuit has light-transmitting characteristic.

14. A film-like article according Claim 2,

wherein the thin film integrated circuit has light-transmitting characteristic.

15. A film-like article according Claim 5,

wherein the thin film integrated circuit has light-transmitting characteristic.

16. A film-like article according Claim 6,

wherein the thin film integrated circuit has light-transmitting characteristic.

17. A film-like article according Claim 7,

wherein the thin film integrated circuit has light-transmitting characteristic.

18. A film-like article according to Claim 1,

wherein the thin film integrated circuit has an insulating film containing nitrogen.

19. A film-like article according to Claim 2,

wherein the thin film integrated circuit has an insulating film containing nitrogen.

20. A film-like article according to Claim 5,

wherein the thin film integrated circuit has an insulating film containing nitrogen.

21. A film-like article according to Claim 6,

wherein the thin film integrated circuit has an insulating film containing nitrogen.

22. A film-like article according to Claim 7,

wherein the thin film integrated circuit has an insulating film containing nitrogen.

23. A film-like article according to Claim 1,

wherein thickness of the thin film integrated circuit is in a range of 0.1 μm to 3 μm.

24. A film-like article according to Claim 2,

wherein thickness of the thin film integrated circuit is in a range of 0.1 μm to 3 μm.

25. A film-like article according to Claim 5,

wherein thickness of the thin film integrated circuit is in a range of 0.1 μm to 3 μm.

26. A film-like article according to Claim 6,

wherein thickness of the thin film integrated circuit is in a range of 0.1 μm to 3 μm.

27. A film-like article according to Claim 7,

wherein thickness of the thin film integrated circuit is in a range of 0.1 μm to 3 μm.

28. A film-like article according to Claim 1,

wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1×10^{19} atoms/cm^3 to 5×10^{20} atoms/cm^3.

29. A film-like article according to Claim 2,

wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1×10^{19} atoms/cm^3 to 5×10^{20} atoms/cm^3.

30. A film-like article according to Claim 5,

wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1×10^{19} atoms/cm^3 to 5×10^{20} atoms/cm^3.

31. A film-like article according to Claim 6,

wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1×10^{19} atoms/cm^3 to 5×10^{20} atoms/cm^3.

32. A film-like article according to Claim 7,

wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1×10^{19} atoms/cm^3 to 5×10^{20} atoms/cm^3.

33. A film-like article according to any one of Claims 28 to 32,

wherein the semiconductor film includes a source, a drain, and a channel region, and

the source, the drain, and the channel region are provided perpendicular to direction of bending the film-like article.

34. A film-like article according to Claim 1,

wherein the film-like article comprises a plurality of thin film integrated circuits,

and

the plurality of thin film integrated circuits are integrated with antennas.

35. A film-like article according to Claim 2,

wherein the film-like article comprises a plurality of thin film integrated circuits,

and

the plurality of thin film integrated circuits are integrated with antennas.

36. A film-like article according to Claim 5,

wherein the film-like article comprises a plurality of thin film integrated circuits,

and

the plurality of thin film integrated circuits are integrated with antennas.

37. A film-like article according to Claim 6,

wherein the film-like article comprises a plurality of thin film integrated circuits,

and

the plurality of thin film integrated circuits are integrated with antennas.

38. A film-like article according to Claim 7,

wherein the film-like article comprises a plurality of thin film integrated circuits, and

the plurality of thin film integrated circuits are integrated with antennas.

39. A film-like article according to Claim 1,

wherein the film-like article is a business card.

40. A film-like article according to Claim 2,

wherein the film-like article is a business card.

41. A film-like article according to Claim 5,

wherein the film-like article is a business card.

42. A film-like article according to Claim 6,

wherein the film-like article is a business card.

43. A film-like article according to Claim 7,

wherein the film-like article is a business card.

44. A method for manufacturing a film-like article, comprising the steps of:

forming a plurality of thin film integrated circuits over a first substrate;

transferring the plurality of thin film integrated circuits to a second substrate;

cutting the second substrate to cut out each of the plurality of thin film integrated circuits;

connecting an antenna to a connection terminal of the thin film integrated circuits; and

enfolding the thin film integrated circuits and the antenna in a base member of the film-like article.

45. A method for manufacturing a film-like article, comprising the steps of:

forming a plurality of thin film integrated circuits over a first substrate;

transferring the plurality of thin film integrated circuits to a second substrate;

cutting the second substrate to cut out each of the plurality of thin film integrated circuits;

connecting an antenna to a connection terminal of the thin film integrated circuits; and

mounting the thin film integrated circuits and the antenna on a surface of a base member of the film-like article.

46. A method for manufacturing a film-like article, comprising the steps of:

forming a plurality of thin film integrated circuits over a first substrate;

transferring the plurality of thin film integrated circuits to a second substrate;

cutting the second substrate to cut out each of the plurality of thin film integrated circuits;

connecting an antenna to a connection terminal of the thin film integrated circuits; and

mounting the thin film integrated circuits and the antenna in a depression on a surface of a base member of the film-like article.

47. A method for manufacturing a film-like article, comprising the steps of:

forming a plurality of thin film integrated circuits over a first substrate;

transferring the plurality of thin film integrated circuits to a second substrate;

cutting the second substrate to cut out each of the plurality of thin film integrated circuits; and

enfolding the thin film integrated circuit in a base member of the film-like article,

forming an antenna on a surface of the base member of the film-like article so that the thin film integrated circuits and the antenna are connected through an opening formed on the base member of the film-like article.

48. A method for manufacturing a film-like article, comprising the step of forming an antenna on a surface of a base member of the film-like article so that a plurality of thin film integrated circuits and the antenna are connected through an opening formed on the base member of the film-like article,

wherein a plurality of thin film integrated circuits are formed over a first substrate,

the plurality of thin film integrated circuits are transferred to a second substrate, and

the second substrate is cut so as to cut out the plurality of thin film integrated circuits.